

InGaAs Larger Area PIN Photodiode

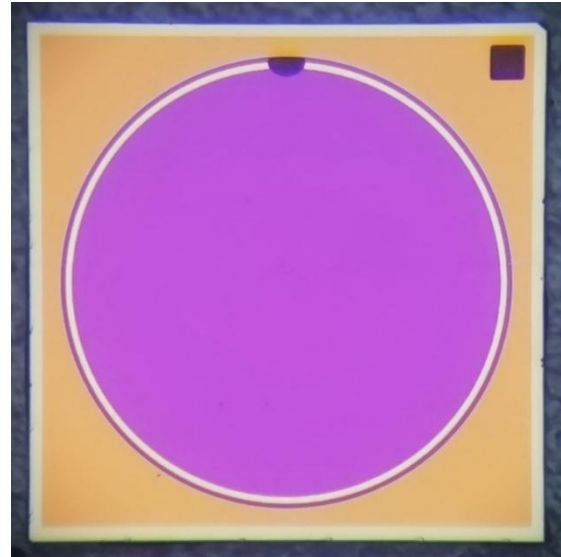
PDPF1000C

Applications

Optical Power Meter
Infrared Rangefinder
Spectroscopy

Features

950 to 1625nm Spectral Response
Planer Structure for High Reliability
Low Dark Current
High Shunt Resistance
High Sensitivity
Low Capacitance



Description

Go!Foton large area Indium Gallium Arsenide (InGaAs) Photodiode consists of pin structure and photo sensitive area of 1 mm diameter with planer structure for high reliability. This PD has photo response in the near infrared spectrum range, between 950 and 1650 nm. This device has very high sensitivity and low noise, making it suitable for industrial applications. PD chips are fabricated at Go!Foton proprietary wafer fab.

Specifications

Electro-Optical Characteristics

Parameter		Min	Typ	Max	Conditions
Active Area Diameter	um		1000		
Responsivity	A/W	0.90	1.0		1.55 um, V = 0 V
		0.80	0.95		1.3 um, V = 0 V
Dark Current	nA		2	300	V = -5 V
Shunt Resistance	MΩ	2	150		V = ±10 mV
Capacitance	pF		100	200	V = 0 V

Condition unless noted: 25 °C, Popt = 1 μW



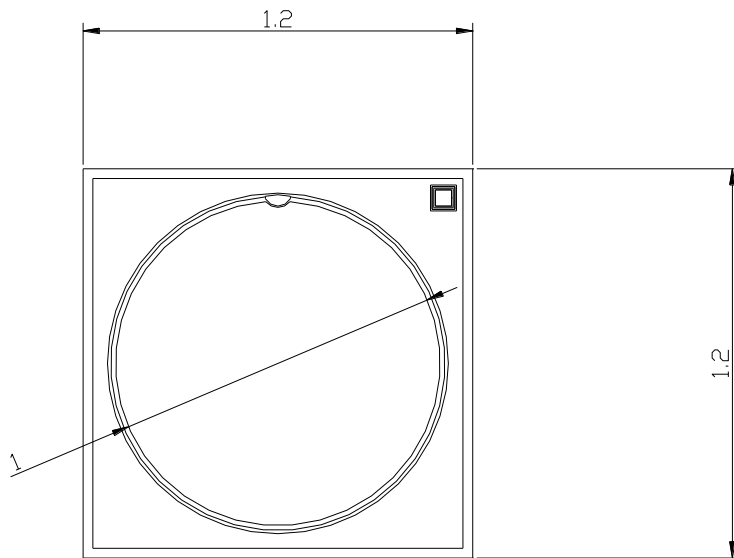
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Absolute Maximum Rating

Parameter	Unit	Min	Max	Conditions
Reverse Current	mA		2	
Reverse Voltage	V		20	
Forward Current	mA		4	
Operating Temperature	°C	-40	85	
Storage Temperature	°C	-40	85	

Drawing



(mm)